

# Panni Wang

## List of Publications by Year in descending order

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25  
papers

484  
citations

687363

13  
h-index

888059

17  
g-index

25  
all docs

25  
docs citations

25  
times ranked

557  
citing authors

#	ARTICLE	IF	CITATIONS
1	Accelerating On-Chip Training with Ferroelectric-Based Hybrid Precision Synapse. ACM Journal on Emerging Technologies in Computing Systems, 2022, 18, 1-20.	2.3	1
2	Exploring argon plasma effect on ferroelectric Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> thin film atomic layer deposition. Journal of Materials Research, 2021, 36, 1206-1213.	2.6	7
3	Impact of Random Phase Distribution in Ferroelectric Transistors-Based 3-D NAND Architecture on In-Memory Computing. IEEE Transactions on Electron Devices, 2021, 68, 2543-2548.	3.0	15
4	Ferroelectric HfO <sub>2</sub> -based synaptic devices: recent trends and prospects. Semiconductor Science and Technology, 2021, 36, 104001.	2.0	25
5	Exploring argon plasma effect on ferroelectric Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> thin film atomic layer deposition. Journal of Materials Research, 2021, 36, 1-8.	2.6	0
6	The Impact of Ferroelectric FETs on Digital and Analog Circuits and Architectures. IEEE Design and Test, 2020, 37, 79-99.	1.2	13
7	Ferroelectric devices and circuits for neuro-inspired computing. MRS Communications, 2020, 10, 538-548.	1.8	22
8	Direct comparison of ferroelectric properties in Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> between thermal and plasma-enhanced atomic layer deposition. Nanotechnology, 2020, 31, 505707.	2.6	45
9	Modeling Multi-states in Ferroelectric Tunnel Junction. , 2020, , .		2
10	Investigating Ferroelectric Minor Loop Dynamics and History Effectâ€”Part I: Device Characterization. IEEE Transactions on Electron Devices, 2020, 67, 3592-3597.	3.0	18
11	Non-volatile, small-signal capacitance in ferroelectric capacitors. Applied Physics Letters, 2020, 117, .	3.3	16
12	Cryogenic behavior of NbO <sub>2</sub> based threshold switching devices as oscillation neurons. Applied Physics Letters, 2020, 116, .	3.3	24
13	Ferroelectric Tunnel Junction Optimization by Plasma-Enhanced Atomic Layer Deposition. , 2020, , .		12
14	Drainâ€”Erase Scheme in Ferroelectric Field-Effect Transistorâ€”Part I: Device Characterization. IEEE Transactions on Electron Devices, 2020, 67, 955-961.	3.0	26
15	Drain-Erase Scheme in Ferroelectric Field Effect Transistorâ€”Part II: 3-D-NAND Architecture for In-Memory Computing. IEEE Transactions on Electron Devices, 2020, 67, 962-967.	3.0	29
16	Investigating Ferroelectric Minor Loop Dynamics and History Effectâ€”Part II: Physical Modeling and Impact on Neural Network Training. IEEE Transactions on Electron Devices, 2020, 67, 3598-3604.	3.0	15
17	Depolarization Field Induced Instability of Polarization States in HfO <sub>2</sub> Based Ferroelectric FET. , 2020, , .		11
18	Ferroelectric Transistors for Synaptic Devices: Challenges and Prospects. , 2020, , .		1

#	ARTICLE	IF	CITATIONS
19	Benchmark of Ferroelectric Transistor-Based Hybrid Precision Synapse for Neural Network Accelerator. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2019, 5, 142-150.	1.5	20
20	Integrated Crossbar Array With Resistive Synapses and Oscillation Neurons. IEEE Electron Device Letters, 2019, 40, 1313-1316.	3.9	26
21	Investigating Dynamic Minor Loop of Ferroelectric Capacitor. , 2019, , .		2
22	Three-Dimensional nand Flash for Vectorâ€“Matrix Multiplication. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2019, 27, 988-991.	3.1	78
23	Exploiting Hybrid Precision for Training and Inference: A 2T-1FeFET Based Analog Synaptic Weight Cell. , 2018, , .		71
24	Low Power Phase Change Memory With Vertical Carbon Nanotube Electrode. IEEE Journal of the Electron Devices Society, 2017, 5, 362-366.	2.1	5
25	Modeling current reduction/or PCM cell with thermal buffer layer. , 2016, , .		0